

[MoB1] Nitrides for Electronics - I

Session Date	July 13 (Mon.), 2026
Session Time	11:15–12:30
Session Room	Room B (Baekrok Hall B, 1F)
Session Chairs	Prof. Xiaohang Li (King Abdullah University of Science and Technology, Saudi Arabia), Prof. Markus Pristovsek (Nagoya University, Japan)

[MoB1–1] [Invited]

11:15–11:45

Recent Progress and Device Advantages of N-Polar GaN/AlN HEMTs

N. Okada¹, F. Yamanaka¹, A. H. Zazuli¹, M. Feng¹, T. Kimoto¹, R. Ninoki¹, N. Hirata¹, H. Danbata¹, A. Hayashiuchi¹, K. Sunai¹, H. Tokumoto¹, Y. Kitamura¹, S. Kurai¹, M. Hiroki², K. Hirama², Y. Taniyasu², and Y. Yamada¹, ¹Yamaguchi University, Japan, ²NTT, Inc., Japan

[MoB1–2] [Invited]

11:45–12:15

MOCVD Growth of III-Nitride Using New Precursors for HEMT: Challenges and Progress

Byeongchan So, Teresa Duarte, Hanspeter Menner, Jannik Richter, Lutz Kirste, Mario Prescher, Patrik Straňák, Sven Maegdefessel, Felix Hoffmann, Fouad Benkhelifa, Stefano Leone, and Rüdiger Quay, Fraunhofer Institute for Applied Solid State Physics IAF, Germany

[MoB1–3]

12:15–12:30

Tunable High-Temperature MOCVD Growth for Strain-Controlled AlN-Based RF GaN HEMT Epitaxy

JongJin Jang, SeongCheol Choi, and DongSik Seo, TES Co., Ltd., Korea